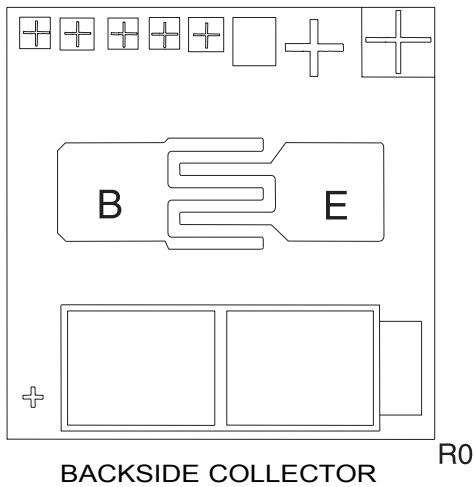


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	14.5 x 14.5 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	2.4 x 2.2 MILS
Emitter Bonding Pad Area	2.4 x 2.2 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

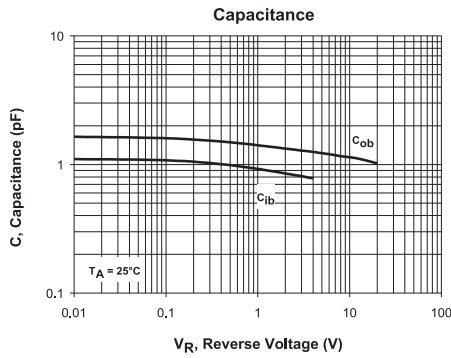
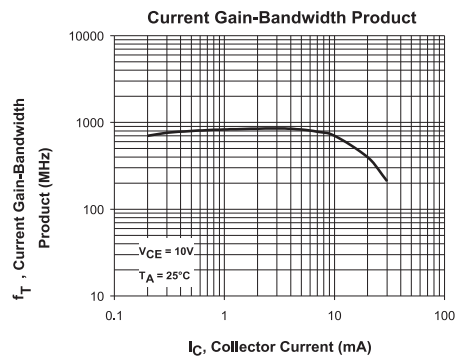
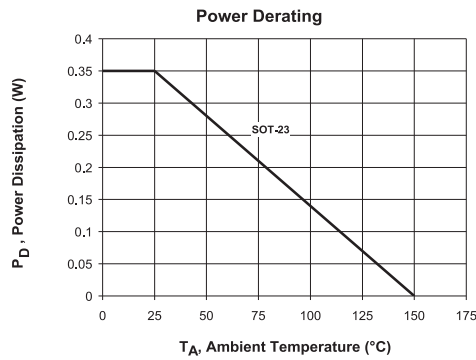
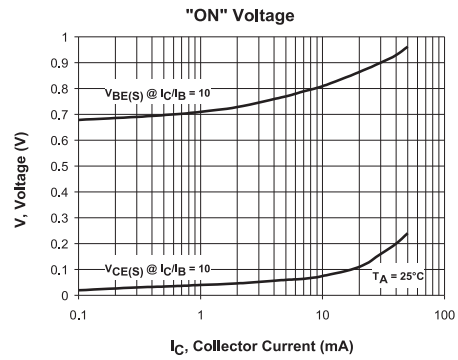
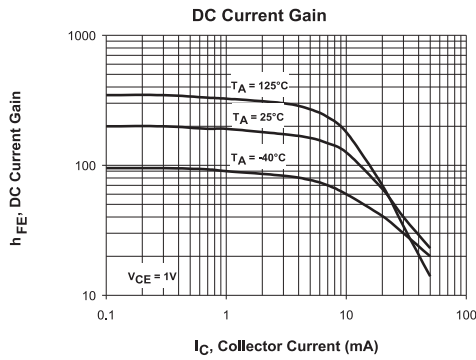
53,730

PRINCIPAL DEVICE TYPES

- CMPT918
- 2N918
- 2N2857
- 2N5179
- 2N5770
- BFY90
- PN3563
- PN3564

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

R2 (1-August 2002)



145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R2 (1-August 2002)